

Data Sheet

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Manufacturers of World Class Discrete Semiconductors

CBR1-L010M SERIES
CBR2-L010M SERIES

SILICON BRIDGE RECTIFIER

CASE B-M

DESCRIPTION

The CENTRAL SEMICONDUCTOR CBR1-L010M, CBR2-L010M series types are silicon single phase full wave bridge rectifiers designed for general purpose applications.

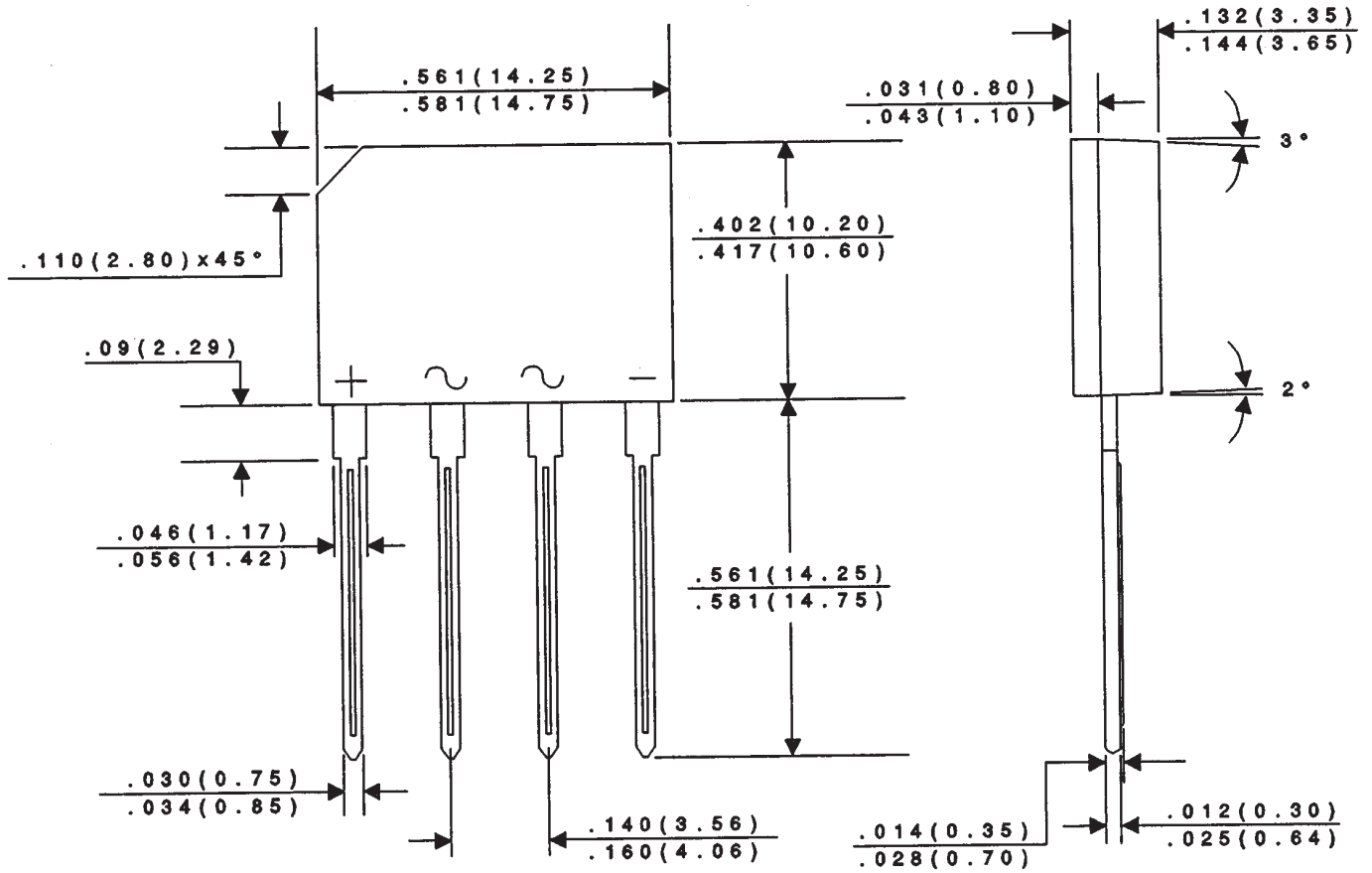
MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

		CBR1- L010M	CBR1- L020M	CBR1- L040M	CBR1- L060M	CBR1- L080M	CBR1- L100M	
		CBR2- L010M	CBR2- L020M	CBR2- L040M	CBR2- L060M	CBR2- L080M	CBR2- L100M	
	SYMBOL							UNITS
Peak Repetitive Reverse Voltage	V _{RRM}	100	200	400	600	800	1000	V
DC Blocking Voltage	V _R	100	200	400	600	800	1000	V
RMS Reverse Voltage	V _{R(RMS)}	70	140	280	420	560	700	V
Average Forward Current (T _A = 50°C) (CBR1-L010M Series)	I _O				1.5			A
Average Forward Current (T _A = 55°C) (CBR2-L010M Series)	I _O				2.0			A
Peak Forward Surge Current (CBR1-L010M Series)	I _{FSM}				50			A
Peak Forward Surge Current (CBR2-L010M Series)	I _{FSM}				60			A
Operating and Storage Junction Temperature	T _J , T _{stg}			-65 to +150				°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
V _F	I _F = 1.0A (CBR1-L010M Series)		1.0	V
V _F	I _F = 2.0A (CBR2-L010M Series)		1.1	V
I _R	V _R = Rated V _{RRM}		10	μA
I _R	V _R = Rated V _{RRM} , T _A = 125°C		500	μA

CASE B-M - MECHANICAL OUTLINE



All Dimensions in Inches (mm).